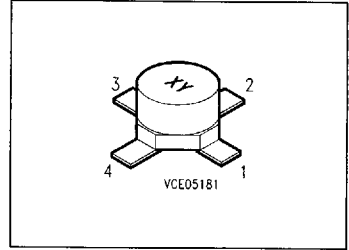


Silicon Schottky Diodes

BAT 14- ... 5 D

- Beam lead technology
- Low dimension
- High performance
- Medium barrier



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration	Package ¹⁾
BAT 14-025 D	42 D	Q62702-A790		Cerec-X
BAT 14-055 D	45 D	Q62702-A793		
BAT 14-095 D	49 D	Q62702-A797		
BAT 14-115 D	41 D	Q62702-A800		

Maximum Ratings

Parameter	Symbol	Values		Unit
		BAT 14-025 D BAT 14-055 D	BAT 14-095 D BAT 14-115 D	
Reverse voltage	V_R	4	4	V
Forward current	I_F	100	50	mA
Junction temperature	T_J	175		°C
Storage temperature range	T_{stg}	- 55 ... + 150		
Operating temperature range	T_{op}	- 55 ... + 150		

¹⁾ For detailed information see chapter Package Outlines.

Electrical Characteristics

at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
Breakdown voltage $I_R = 10\ \mu\text{A}$	$V_{(BR)}$	4	–	–	V	
Diode capacitance $V_R = 0, f = 1\ \text{MHz}$	C_T	–	0.37	0.42	pF	
BAT 14-025 D		–	0.27	0.32		
BAT 14-055 D		–	0.21	0.22		
BAT 14-115 D		–	0.17	0.19		
Forward voltage $I_F = 1\ \text{mA}$	V_F	BAT 14-025 D	–	0.45	–	V
		BAT 14-055 D	–	0.47	–	
		BAT 14-095 D	–	0.49	–	
		BAT 14-115 D	–	0.50	–	
$I_F = 10\ \text{mA}$	BAT 14-025 D	–	0.55	–		
	BAT 14-055 D	–	0.57	–		
	BAT 14-095 D	–	0.60	–		
	BAT 14-115 D	–	0.65	–		
Single sideband noise figure $F_{IF} = 1.5\ \text{dB}, P_{LO} = 0\ \text{dBm}, f_{IF} = 10.7\ \text{MHz}$	F_{SSB}	$f = 3\ \text{GHz}$	–	6.0	–	dB
		$f = 6\ \text{GHz}$	–	6.5	–	
		$f = 9.3\ \text{GHz}$	–	6.5	–	
		$f = 16\ \text{GHz}$	–	7.0	–	
			–	7.0	–	
Differential forward resistance $I_F = 10/50\ \text{mA}$	r_1	BAT 14-025 D	–	3.5	–	Ω
		BAT 14-055 D	–	4.0	–	
		BAT 14-095 D	–	7.0	–	
		BAT 14-115 D	–	10.0	–	